

TN6716A



NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.2A. Sourced from Process 38. See TN6715A for characteristics.

Absolute Maximum Ratings*

T_{A = 25°C unless otherwise noted}

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	Α
T _{J, ⊺stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristic	Max	Units
		T _A =25°C	
P _D	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
R _θ JC	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

NPN General Purpose Amplifier

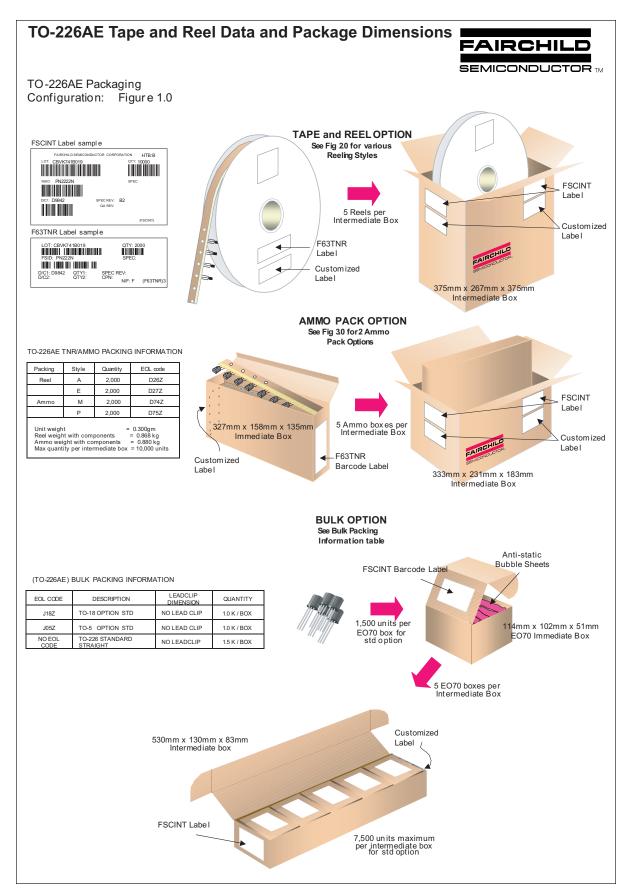
(continued)

Electrical Characteristics

 $T_{\text{A}\,=\,25^{\circ}\text{C}\,\text{unless otherwise noted}}$

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1 mA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40 V		100	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5 V		10	uA
ON CHA	RACTERISTICS				
h _{FE}	DC Current Gain	$I_{C} = 50 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 250 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 1 \text{ V}$	80 50 20	250	-
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 250 mA, I _B = 10 mA I _C = 250 mA, I _B = 25 mA		0.5 0.35	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 250 mA, V _{CE} = 1.0 V		1.2	V
SMALL S	SIGNAL CHARACTERISTICS		•		
C _{cb}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		30	pF
hfe	Small Signal Current Gain	I _C = 200 mA,V _{CE} = 5 V,f=20MHz	2.5	25	MHz

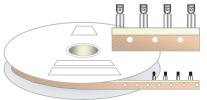
^{*}Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 1.0\%$



TO-226AE Tape and Reel Data and Package Dimensions, continued

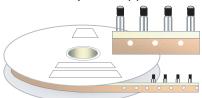
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option"A" (H)



Style "A", D26Z, D70Z (s/h)

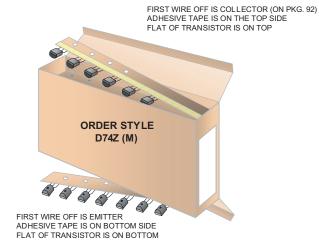
Machine Option"E" (J)



Style "E", D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

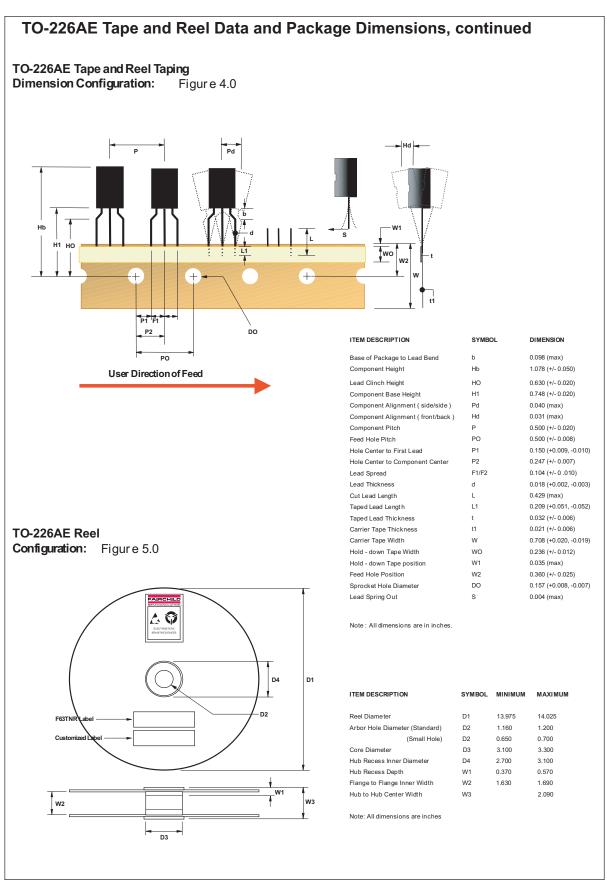
Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

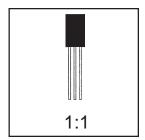
ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



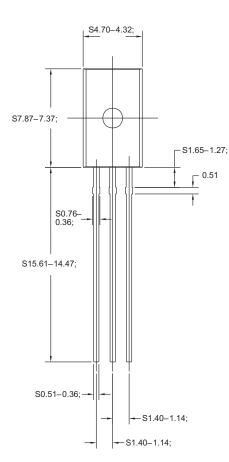
TO-226AE Tape and Reel Data and Package Dimensions, continued TO-226AE (FS PKG Code 95, 99)

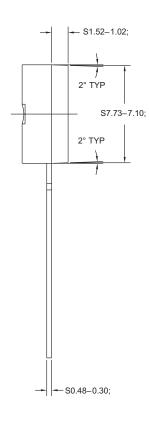




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

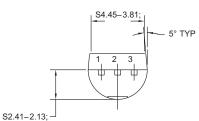
Part Weight per unit (gram): 0.300





Ζ	99	95	
1	Е	Е	
2	В	С	
3	С	В	

For leadformed option ordering, refer to Tape & Reel data information.



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